# Innogration (Suzhou) Co., Ltd.

P1dB

Eff(%)

56. 7

58.9

57.7

P1dB

Gain (dB)

17.53

17.72

17.18

Document Number: ITEH27025C6 Preliminary Datasheet V1.0

## 30W,28V Plastic RF LDMOS Transistor

## Description

Freq

(MHz)

2400

2450

2500

The ITEH27025C6 is a 30-watt, highly rugged, LDMOS transistor, designed for any general applications at frequencies up to 2.5GHz, in 10\*6mm QFN plastic package, supporting surface mounted on PCB through high density grounding vias.

P1dB

(W)

28.8

25.8

22.7

•Typical 2.4-2.5GHz Class AB RF Performance (On Innogration fixture with device soldered). VDS=**28V**, Idq=10mA

# internal and the second

P3dB

Eff(%)

58

60

59

ITEH27025C6

### Features

• High Efficiency and Linear Gain Operations

P1dB

(dBm)

44.59

44.11

43.56

- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation

P3dB

(W)

32.8

30.0

29.0

• Pb-free, RoHS-compliant

P3dB

(dBm)

45.16

44.77

44.61

#### **Suitable Applications**

• Broadcast and Industrial, Scientific and Medical applications in the frequency range from HF to 2.5GHz

#### **Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
DrainSource Voltage	V <sub>DSS</sub>	+65	Vdc
GateSource Voltage	$V_{GS}$	-10 to +10	Vdc
Operating Voltage	$V_{DD}$	+28	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	Τ <sub>J</sub>	+225	°C

#### **Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Rejc	0.8	°C/W
T <sub>C</sub> = 85°C, T <sub>J</sub> =200°C, DC test	K⊕JC	0.0	-0/00

#### **Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22A114)	Class 2

#### Table 4. Electrical Characteristics (TA = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DC Characteristics		-	-	· · · · · · · · · · · · · · · · · · ·	
Drain-Source Voltage	$V_{(BR)DSS}$		65		V



# Innogration (Suzhou) Co., Ltd.

Document Number: ITEH27025C6 Preliminary Datasheet V1.0

V <sub>GS</sub> =0, I <sub>DS</sub> =100uA				
Zero Gate Voltage Drain Leakage Current		 	1	^
$(V_{DS} = 28V, V_{GS} = 0 V)$	I <sub>DSS</sub>	 		μΑ
GateSource Leakage Current		 	1	^
$(V_{GS} = 11 \text{ V}, V_{DS} = 0 \text{ V})$	I <sub>GSS</sub>	 	l l	μΑ
Gate Threshold Voltage	V (45)	 2		V
$(V_{DS} = 28V, I_D = 600 \mu A)$	V <sub>GS</sub> (th)	 2		V
Gate Quiescent Voltage	V	 2.5		V
(V <sub>DD</sub> = 28V, I <sub>D</sub> = 10mA, Measured in Functional Test)	$V_{GS(Q)}$	 2.5		V

Load Mismatch (In Innogration Test Fixture, 50 ohm system):  $V_{DD} = 28 \text{Vdc}$ ,  $I_{DQ} = 10 \text{ mA}$ , f = 2500 MHz

VSWR 10:1 at 30W pulse CW Output Power No Device Degradation

Figure 1:Pin Definition(Top View)



Pin No.	Symbol	Description
8,9,10,11,14,15,16,17	Vgs/RF In	Vgs and RF input
26,27,28,29,32,33,34,35	Vds/RF out	Vds and RF output
2,5,7,12,13,18,20,23,25,30,31,36	GND	DC/RF Ground
Others	NC	No connection
Package Base	GND	DC/RF Ground.

# Reference Circuit of Test Fixture Assembly Diagram 2400-2500MHz RO4350B 20mils

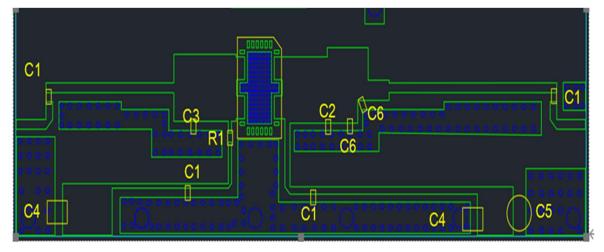


Figure 2. Test Circuit Component Layout



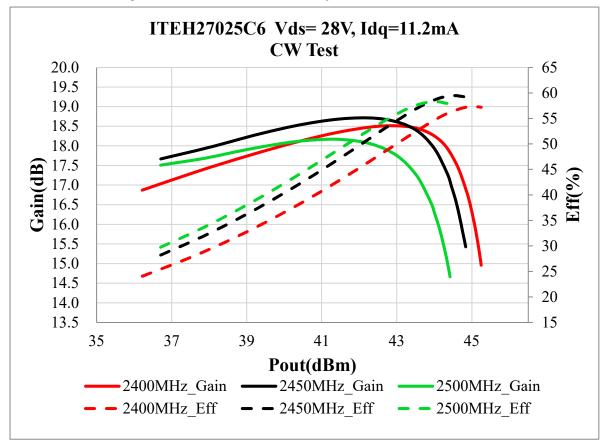
## Innogration (Suzhou) Co., Ltd.

**Table 5. Test Circuit Component Designations and Values** 

Component	Value	Quantity
U1	ITEH27025C6	1
C1	12pF	4
C4	10uF/63V	2
R1	10 Ω	1
C5	470uF/63V	1
C3	1.5pF	1
C2	1pF	1
C6	0.6pF	2

#### TYPICAL CHARACTERISTICS

Figure 3. Power Gain and Drain Efficiency as function of Power Out

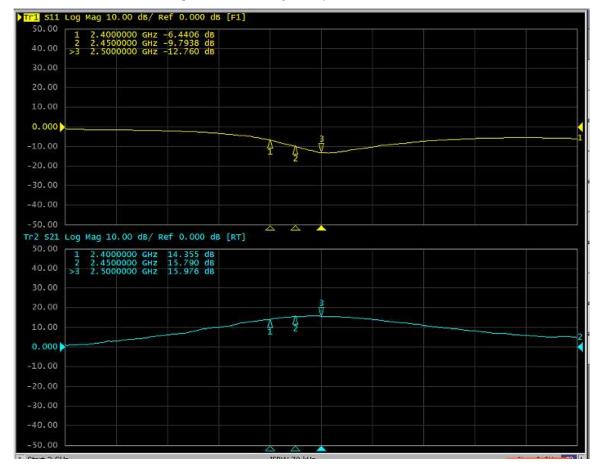




Document Number: ITEH27025C6 Preliminary Datasheet V1.0

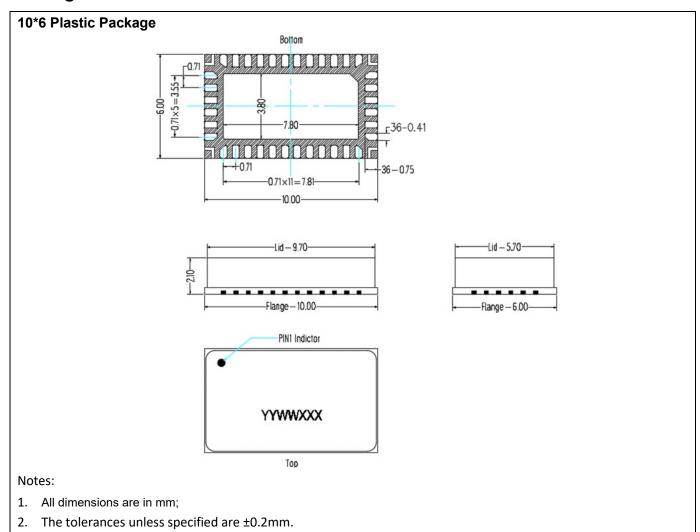


Figure 4.Network analyzer output S11/S21



Document Number: ITEH27025C6 Preliminary Datasheet V1.0

## **Package Dimensions**



#### Revision history

Table 7. Document revision history

Date	Revision	Datasheet Status
2023/10/23	Rev 1.0	Preliminary Datasheet

#### Application data based on ZXY-23-13

#### **Disclaimers**

Specifications are subject to change without notice. Innogration believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Innogration for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Innogration . Innogration makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Innogration in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Innogration products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innogration product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility. For any concerns or questions related to terms or conditions, pls check with Innogration and authorized distributors Copyright © by Innogration (Suzhou) Co.,Ltd.